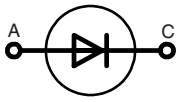
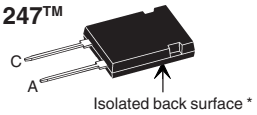
HiPerDyn™ Schottky Diode
(Electrically Isolated Back Surface)

I_{FAV} = 17 A
V_{RRM} = 600 V
t_{rr} = 45 ns

V_{RSM} V	V_{RRM} V	Type
600	600	DSS 17-06CR



ISOPLUS 247™



A = Anode, C = Cathode

* Patent pending

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		50	A
I_{FAVM}	T_C = 95°C; rectangular, d = 0.5	17	A
I_{FRM}	t_P < 10 µs; rep. rating, pulse width limited by T_{VJM}	tbd	A
I_{FSM}	T_{VJ} = 45°C; t_p = 10 ms (50 Hz), sine	200	A
E_{AS}	I_{AS} = 2 A; L = 100 µH; T_{VJ} = 25°C; non-repetitive	0.2	mJ
I_{AR}	V_A = 1.5·V_R typ.; f = 10 kHz; repetitive	0.2	A
T_{VJ}		-55...+175	°C
T_{VJM}		175	°C
T_{stg}		-55...+150	°C
P_{tot}	T_C = 25°C	105	W
V_{ISOL}	50/60 Hz RMS; I_{ISOL} ≤ 1 mA	2500	V~
F_C	mounting force with clip	20...120	N
Weight	typical	6	g

Symbol	Conditions	Characteristic Values typ.	max.	
I_R ①	T_{VJ} = 25°C V_R = V_{RRM}		0.5	mA
	T_{VJ} = 125°C V_R = V_{RRM}		5	mA
V_F ②	I_F = 15 A; T_{VJ} = 125°C		2.71	V
	T_{VJ} = 25°C		3.32	V
R_{thJC}			1.4	K/W
R_{thCH}		0.25		K/W
t_{rr}	I_F = 10 A; -di/dt = 100 A/µs; V_R = 100 V; T_{VJ} = 25°C	45		ns
I_{RM}	V_R = 100 V; I_F = 10 A; -di_F/dt = 100 A/µs T_{VJ} = 25°C	4.0		A

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
② Pulse Width = 300 µs, Duty Cycle < 2.0 %

Data according to IEC 60747 and per diode unless otherwise specified.

Features

- Silicon chip on Direct-Copper-Bond substrate
  - High power dissipation
  - Isolated mounting surface
  - 2500V electrical isolation
- Low cathode to tab capacitance (<25 pF)
- International standard package
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I_{RM}-values
- Soft recovery behaviour
- Epoxy meets UL 94V-0
- Isolated and UL registered E153432

Applications

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{RM} reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Dimensions see Outlines.pdf

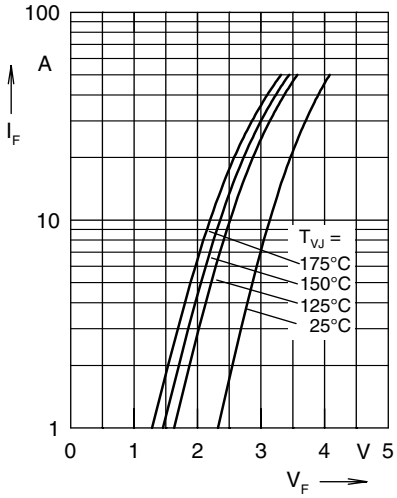


Fig. 1 Maximum forward voltage drop characteristics

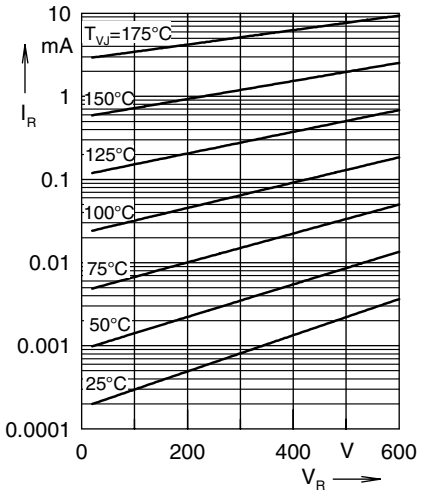


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

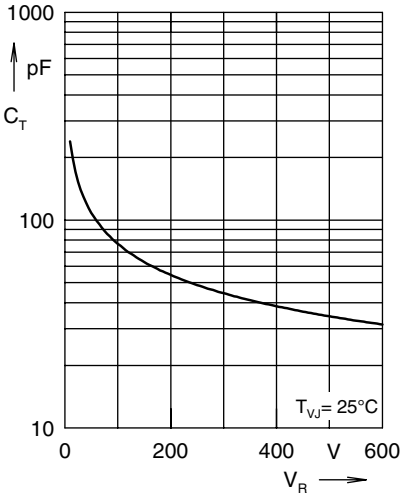


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

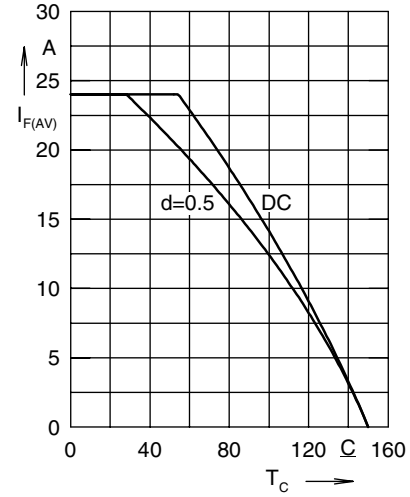


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

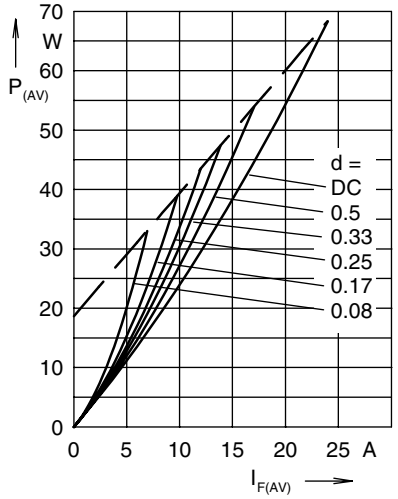


Fig. 5 Forward power loss characteristics

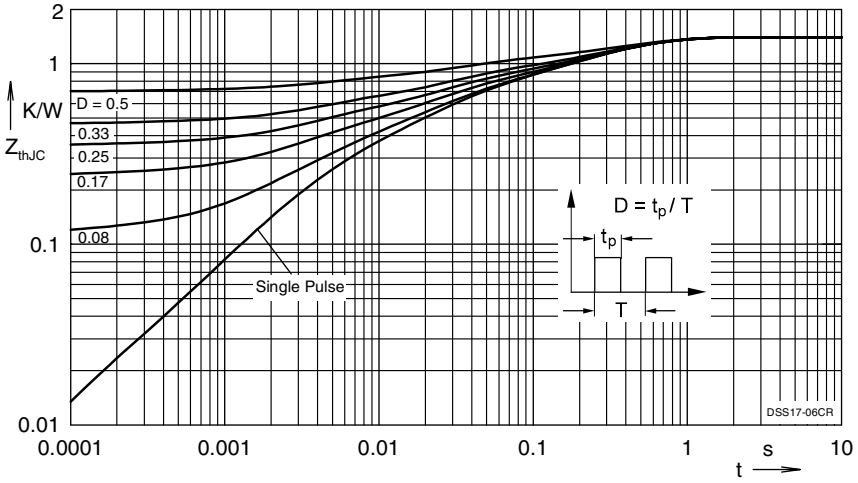


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

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